

S/N Unknown

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Kie Y. Ahn et al.	Examiner:	Unknown
Serial No.:	Unknown	Group Art Unit:	Unknown
Filed:	Herewith	Docket:	1303.070US2
Title:	LANTHANIDE DOPED TiO _x DIELECTRIC FILMS		

INFORMATION DISCLOSURE STATEMENT

MS Patent Application
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement.

Pursuant to 37 C.F.R. §1.98(d), copies of the listed documents are not provided as these references were previously cited by or submitted to the U.S. Patent Office in connection with Applicants' prior U.S. application, Serial No. 10/219878, filed on August 15, 2002, which is relied upon for an earlier filing date under 35 U.S.C. §120.

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

KIE Y. AHN ET AL.

By their Representatives,

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Date 27 February 2004

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Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE
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Application Number	Unknown
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First Named Inventor	Ahn, Kie
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US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
	US20020089023	07/11/2002	Yu, Zhiyi , et al.	257	411	01/05/2001
	US20020155688	10/24/2002	Ahn, Kie Y. et al.			
	US20020155689	10/24/2002	Ahn, Kie Y., et al.	29	76	02/11/2002
	US20020192974	12/19/2002	Ahn, Kie Y., et al.	438	722	06/13/2001
	US20030017717	01/23/2003	Ahn, Kie Y., et al.	438	768	07/18/2001
	US-4,215,156	07/29/1980	Dalal, Hormazdyar M., et al.	427	84	08/26/1977
	US-4,333,808	06/08/1982	Bhattacharyya, Arup , et al.	204	192 D	02/13/1981
	US-4,394,673	07/19/1983	Thompson, Richard D., et al.	357	15	09/29/1980
	US-4,399,424	04/16/1983	Rigby, Leslie J.	338	34	10/05/1981
	US-4,413,022	11/01/1983	Suntola, Tuomo S., et al.	427	255.2	06/21/1979
	US-4,647,947	03/03/1987	Takeoka, Yoshikatsu , et al.	346	135.1	09/13/1985
	US-4,920,071	04/24/1990	Thomas, Michael	437	188	08/18/1987
	US-5,055,319	10/08/1991	Bunshah, Rointan F., et al.	427	38	04/02/1990
	US-5,595,606	01/21/1997	Fujikawa, Yuichiro , et al.	118	725	04/18/1996
	US-5,795,808	08/18/1998	Park, Bo	438	301	11/12/1996
	US-5,801,105	09/01/1998	Yano, Yoshihiko , et al.	438	785	06/14/1996
	US-5,810,923	09/22/1998	Yano, Yoshihiko , et al.	117	84	05/10/1996
	US-5,822,256	10/13/1998	Bauer, Mark , et al.	365	200	03/05/1997
	US-5,828,080	10/27/1998	Yano, Yoshihiko , et al.	257	43	04/17/1995
	US-5,840,897	11/24/1998	Kirlin, Peter , et al.	546	2	06/07/1995
	US-6,013,553	01/11/2000	Wallace, Robert , et al.	438	287	07/15/1998
	US-6,020,024	02/01/2000	Maiti, Bikas , et al.	427	248.1	08/04/1997
	US-6,027,961	02/22/2000	Maiti, Bikas , et al.	438	199	06/30/1998
	US-6,057,271	05/02/2000	Kenjiro, Higaki , et al.	505	475	06/07/1995
	US-6,059,885	05/09/2000	Ohashi, Tadashi , et al.	118	730	12/16/1997
	US-6,093,944	07/25/2003	VanDover, Robert B.	257	310	06/04/1998
	US-6,110,529	08/29/2000	Gardiner, R. A., et al.	427	250	06/07/1995
	US-6,171,900	01/09/2001	Sun, Shi-Chung	438	240	04/15/1999

EXAMINER**DATE CONSIDERED**

Substitute Disclosure Statement Form (PTO-1449)

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Attorney Docket No: 1303.070US2

	US-6,203,613	03/20/2001	Gates, Stephen M., et al.	117	104	10/19/1999
	US-6,211,035	04/03/2001	Moise, Theodore , et al.	438	396	09/09/1999
	US-6,225,168	05/01/2001	Gardner, Mark , et al.	438	287	06/04/1998
	US-6,297,539	10/02/2001	Ma, Yanjun , et al.	257	410	07/06/2000
	US-6,303,481	10/16/2001	Park, Dong	438	591	12/29/2000
	US-6,368,941	04/09/2002	Chen, Tai-Ju , et al.	438	424	11/08/2000
	US-6,380,579	04/30/2002	Nam, Sang-don , et al.	257	306	04/11/2000
	US-6,387,712	05/14/2002	Yano, Yoshihiko , et al.	438	3	12/03/1999
	US-6,391,769	05/21/2002	Lee, Jong-myeong , et al.	438	643	03/14/2000
	US-6,432,779	08/13/2002	Hobbs, Christopher , et al.	438	287	01/30/2001
	US-6,445,023	09/03/2002	Vaartstra, Brian , et al.	257	295	03/16/1999
	US-6,458,701	10/01/2002	Chae, Yun-sook , et al.	438	680	10/12/2000
	US-6,461,436	10/08/2002	Campbell, Philip H., et al.	118	715	10/15/2001
	US-6,465,334	10/15/2002	Buynoski, Matthew S., et al.	438	591	10/05/2000
	US-6,521,911	02/18/2003	Parsons, Gregory N., et al.	257	52	07/19/2001
	US-6,534,420	03/18/2003	Ahn, Kie Y., et al.	438	768	07/18/2001
	US-6,602,338	08/05/2003	Chen, San-Yuan , et al.	106	287.19	04/11/2001

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T ²
	JP-2001-332546	11/30/2001		H01L	21/316	

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		AARIK, JAAN , et al., "Atomic layer growth of epitaxial TiO/sub 2/ thin films from TiCl/sub 4/ and H/sub 2/O on alpha -Al/sub 2/O/sub 3/ substrates", <u>Journal of Crystal Growth</u> , 242(1-2), (2002), 189-198	
		AARIK, JAAN , et al., "Texture development in nanocrystalline hafnium dioxide thin films grown by atomic layer deposition", <u>Journal of Crystal Growth</u> , 220(1-2), (2000), 105-113	

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Sheet 3 of 6	Attorney Docket No: 1303.070US2												

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		BUNSHAH, ROINTAN F., et al., "Deposition Technologies for Films and Coatings: Developments and Applications", <u>Park Ridge, N.J., U.S.A. : Noyes Publications, (1982),102-103</u>	
		CHENG, BAOHONG , et al., "The Impact of High-k Gate Dielectrics and Metal Gate Electrodes on Sub-100nm MOSFET's", <u>IEEE Transactions on Electron Devices, 46(7), (July 1999),1537-1544</u>	
		DESU, S B., "Minimization of Fatigue in Ferroelectric Films", <u>Physica Status Solidi A, 151(2), (1995),467-480</u>	
		ENGELHARDT, M. , "Modern Applications of Plasma Etching and Patterning in Silicon Process Technology", <u>Contributions to Plasma Physics, 39(5), (1999),473-478</u>	
		FUYUKI, TAKASHI , et al., "Electronic Properties of the INTERface between Si and TiO2 Deposited at Very Low Temperatures", <u>(1986),1288-1291</u>	
		GARTNER, M , et al., "Spectroellipsometric characterization of lanthanide-doped TiO2 films obtained via the sol-gel technique", <u>Thin Solid Films, 234(1-2), (1993),561-565</u>	
		GELLER, S. , et al., "Crystallographic Studies of Perovskite-like Compounds. II. Rare Earth Aluminates", <u>Acta Cryst. Vol. 9, (May 1956),1019-1025</u>	
		GIESS, E. A., et al., "Lanthanide gallate perovskite-type substrates for epitaxial, high-T/sub c/ superconducting Ba/sub 2/YCu/sub 3/O/sub 7- delta / films", <u>IBM Journal of Research and Development, 34(6), (November 1990),916-926</u>	
		HIRAYAMA, MASAKI , et al., "Low-Temperature Growth of High-Integrity Silicon Oxide Films by Oxygen Radical Generated in High Density Krypton Plasma", <u>International Electron Devices Meeting 1999. Technical Digest, (1999),249-252</u>	
		HUBBARD, K. J., et al., "Thermodynamic stability of binary oxides in contact with silicon", <u>Journal of Materials Research, 11(11), (November 1996),2757-2776</u>	
		HUNT, C. E., et al., "Direct bonding of micromachined silicon wafers for laser diode heat exchanger applications", <u>Journal of Micromechanics and Microengineering, 1(3), (September 1991),152-156</u>	
		IDDLES, D M., et al., "Relationships between dopants, microstructure and the microwave dielectric properties of ZrO2-TiO2-SnO2 ceramics", <u>Journal of Materials Science, 27(23), (December 1992),6303-6310</u>	
		JEON, SANGHUN , et al., "Excellent electrical characteristics of lanthanide (Pr, Nd, Sm, Gd, and Dy) oxide and lanthanide-doped oxide for MOS gate dielectric applications", <u>Electron Devices Meeting, 2001. IEDM Technical Digest. International, (2001),471-474</u>	
		JEONG, CHANG-WOOK , et al., "Plasma-Assisted Atomic Layer Growth of High-Quality Aluminum Oxide Thin Films", <u>Japanese Journal of Applied Physics, Part 1: Regular Papers and Short Notes and Review Papers, 40(1), (January 2001),285-289</u>	

EXAMINER

DATE CONSIDERED

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>	<table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td colspan="2" style="text-align: center;"><i>Complete if Known</i></td> </tr> <tr> <td style="width: 50%;">Application Number</td> <td>Unknown</td> </tr> <tr> <td>Filing Date</td> <td>Even Date Herewith</td> </tr> <tr> <td>First Named Inventor</td> <td>Ahn, Kie</td> </tr> <tr> <td>Group Art Unit</td> <td>Unknown</td> </tr> <tr> <td>Examiner Name</td> <td>Unknown</td> </tr> </table>	<i>Complete if Known</i>		Application Number	Unknown	Filing Date	Even Date Herewith	First Named Inventor	Ahn, Kie	Group Art Unit	Unknown	Examiner Name	Unknown
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Sheet 4 of 6	Attorney Docket No: 1303.070US2												

		KAWAI, Y , et al., "Ultra-low-temperature growth of high-integrity gate oxide films by low-energy ion-assisted oxidation", <u>Applied Physics Letters</u> , 64(17), (April 1994),2223-2225	
		KEOMANY, D , et al., "Sol gel preparation of mixed cerium-titanium oxide thin films", <u>Solar Energy Materials and Solar Cells</u> , 33(4), (August 1994),429-441	
		KIM, C T., et al., "Application of Al ₂ O ₃ Grown by Atomic Layer Deposition to DRAM and FeRAM", <u>International Symposium in Integrated Ferroelectrics</u> , (March 2000),316	
		KIM, D. , et al., "Atomic Control of Substrate Termination and Heteroepitaxial Growth of SrTiO ₃ /LaAlO ₃ Films", <u>Journal of the Korean Physical Society</u> , 36(6), (June 2000),444-448	
		KIM, TAESEOK , et al., "Correlation between strain and dielectric properties in ZrTiO/sub 4/ thin films", <u>Applied Physics Letters</u> , 76(21), (May 2000),3043-3045	
		KRAUTER, G. , et al., "Room Temperature Silicon Wafer Bonding with Ultra-Thin Polymer Films", <u>Advanced Materials</u> , 9(5), (1997),417-420	
		KUKLI, KAUPÖ , "Atomic Layer Deposition of Titanium Oxide from TiI ₄ and H ₂ O ₂ ", <u>Chemical Vapor Deposition</u> , 6(6), (2000),303-310	
		KUKLI, K , et al., "Controlled growth of yttrium oxysulphide thin films by atomic layer deposition", <u>Materials Science Forum</u> , 315-317, (1999),216-221	
		LEE, A E., et al., "Epitaxially grown sputtered LaAlO ₃ films", <u>Applied Physics Letters</u> , 57(19), (November 1990),2019-2021	
		LEE, CHENG-CHUNG , et al., "Ion-assisted deposition of silver films", <u>Thin Solid Films</u> , vol. 359, (2000),95-97	
		LEE, DONG H., et al., "Metalorganic chemical vapor deposition of TiO/sub 2/:N anatase thin film on Si substrate", <u>Applied Physics Letters</u> , 66(7), (February 1995),815-816	
		LEE, L P., et al., "Monolithic 77 K dc SQUID magnetometer", <u>Applied Physics Letters</u> , 59(23), (December 1991),3051-3053	
		LESKELA, M , et al., "ALD precursor chemistry: Evolution and future challenges", <u>Journal de Physique IV (Proceedings)</u> , 9(8), (September 1999),837-852	
		LIU, C. T., "Circuit Requirement and Integration Challenges of Thin Gate Dielectrics for Ultra Small MOSFETs", <u>International Electron Devices Meeting 1998. Technical Digest</u> , (1998),747-750	
		LUCOVSKY, G , et al., "Microscopic model for enhanced dielectric constants in low concentration SiO/sub 2/-rich noncrystalline Zr and Hf silicate alloys", <u>Applied Physics Letters</u> , 77(18), (October 2000),2912-2914	
		MARTIN, et al., "Ion-beam-assisted deposition of thin films", <u>Applied Optics</u> , 22(1), (1983),178-184	
		MOLODYK, A A., et al., "Volatile Surfactant-Assisted MOCVD: Application to LaAlO ₃ Thin Film Growth", <u>Chemical Vapor Deposition</u> , 6(3), (June 2000),133-138	

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	MOLSA, HEINI , et al., "Growth of yttrium oxide thin films from beta -diketonate precursor", <u>Advanced Materials for Optics and Electronics</u> , 4(6), (November-December 1994),389-400	
	MULLER, D. A., et al., "The electronic structure at the atomic scale of ultrathin gate oxides", <u>Nature</u> , 399(6738), (June 24, 1999),758-61	
	NAKAJIMA, ANRI , et al., "NH/sub 3/-annealed atomic-layer-deposited silicon nitride as a high-k gate dielectric with high reliability", <u>Applied Physics Letters</u> , 80(7), (February 2002),1252-1254	
	NEUMAYER, D A., et al., "Materials characterization of ZrO/sub 2/-SiO/sub 2/ and HfO/sub 2/-SiO/sub 2/ binary oxides deposited by chemical solution deposition", <u>Journal of Applied Physics</u> , 90(4), (August 15, 2001),1801-1808	
	NIEMINEN, MINNA , et al., "Formation and stability of lanthanum oxide thin films deposited from B-diketonate precursor", <u>Applied Surface Science</u> , 174(2), (April 16, 2001),155-165	
	OHRING, MILTON , "The Materials Science of Thin Films", <u>Boston : Academic Press</u> , (1992),118,121,125	
	OSTEN, H. J., et al., "High-k gate dielectrics with ultra-low leakage current based on praseodymium oxide", <u>International Electron Devices Meeting 2000. Technical Digest. IEDM</u> , (2000),653-656	
	PARK, JAEHOO , et al., "Chemical vapor deposition of HfO/sub 2/ thin films using a novel carbon-free precursor: characterization of the interface with the silicon substrate", <u>Journal of the Electrochemical Society</u> , 149(1), (2002),G89-G94	
	PARK, BYUNG-EUN , et al., "Electrical properties of LaAlO3/Si and Sr0.8Bi2.2Ta2O9/LaAlO3/Si structures", <u>Applied Physics Letters</u> , 79(6), (August 2001),806-808	
	QI, WEN-JIE , et al., "MOSCAP and MOSFET characteristics using ZrO2 gate dielectric deposited directly on Si", <u>Electron Devices Meeting, 1999. IEDM Technical Digest. International</u> , (1999),145-148	
	RAYNER JR., G , et al., "The structure of plasma-deposited and annealed pseudo-binary ZrO2-SiO2 alloys", <u>Materials Research Society Symposium - Proceedings</u> , 611, (2000),C131-C139	
	RITALA, MIKKO , "Atomic Layer Epitaxy Growth of Titanium, Zirconium and Hafnium Dioxide Thin Films", <u>Annales Academiae Scientiarum Fennicae</u> , (1994),24-25	
	ROTONDARO, A L., et al., "Advanced CMOS Transistors with a Novel HfSiON Gate Dielectric", <u>Symposium on VLSI Technology Digest of Technical Papers</u> , (2002),148-149	
	SAITO, YUJI , et al., "Advantage of Radical Oxidation for Improving Reliability of Ultra-Thin Gate Oxide", <u>2000 Symposium on VLSI Technology Digest of Technical Papers</u> , (2000),176-177	

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Sheet 6 of 6	Attorney Docket No: 1303.070US2												

		SAITO, YUJI , et al., "High-Integrity Silicon Oxide Grown at Low-Temperature by Atomic Oxygen Generated in High-Density Krypton Plasma", <u>Extended Abstracts of the 1999 International Conference on Solid State Devices and Materials</u> , (1999),152-153	
		SHANWARE, A , et al., "Reliability evaluation of HfSiON gate dielectric film with 12.8 A SiO2 equivalent thickness", <u>International Electron Devices Meeting. Technical Digest</u> , (2001),137-140	
		SHIN, CHANG H., et al., "Fabriation and Characterization of MFISFET using Al2O3 Insulating Layer for Non-Volatile Memory", <u>12th International Symposium in Integrated Ferroelectrics</u> , (March 2000),1-9	
		SNEH, OFER , "Thin film atomic layer deposition equipment for semiconductor processing", <u>Thin Solid Films</u> , 402(1-2), (January 2002),248-261	
		SONG, HYUN-JUNG , et al., "Atomic Layer Deposition of Ta2O5 Films Using Ta(OC2H5)5 and NH3", <u>Ultrathin SiO/sub 2/ and High-K Materials for ULSI Gate Dielectrics. Symposium</u> , (1999),469-471	
		SUNTOLA, T , "Atomic layer epitaxy", <u>Thin Solid Films</u> , 216(1), (August 28, 1992),84-89	
		SUNTOLA, T. , "Atomic Layer Epitaxy", <u>Handbook of Crystal Growth</u> , 3; <u>Thin Films of Epitaxy, Part B: Growth Mechanics and Dynamics</u> , Amsterdam,(1994),602-663	
		TAKEMOTO, J. H., et al., "Microstrip Resonators and Filters Using High-TC Superconducting Thin Films on LaAlO3", <u>IEEE Transaction on Magnetics</u> , 27(2), (March 1991),2549-2552	
		TARRE, A , et al., "Comparative study of low-temperature chloride atomic-layer chemical vapor deposition of TiO2 and SnO2", <u>Applied Surface Science</u> , 175-176, (May 2001),111-116	
		VAN DOVER, R B., "Amorphous lanthanide-doped TiOx dielectric films", <u>Applied Physics Letters</u> , 74(20), (May 1999),3041-3043	
		VIIROLA, H , "Controlled growth of antimony-doped tin dioxide thin films by atomic layer epitaxy", <u>Thin Solid Films</u> , 251, (November 1994),127-135	
		VIIROLA, H , "Controlled growth of tin oxide thin films by atomic layer epitaxy", <u>Thin Solid Films</u> , 249(2), (September 1994),144-149	
		VISOKAY, M R., "Application of HfSiON as a gate dielectric material", <u>Applied Physics Letters</u> , 80(17), (April 2002),3183-3185	
		WILK, G D., et al., "Hafnium and zirconium silicates for advanced gate dielectrics", <u>Journal of Applied Physics</u> , 87(1), (January 2000),484-492	
		WILK, G. D., et al., "High-K gate dielectrics: Current status and materials properties considerations", <u>Journal of Applied Physics</u> , 89(10), (May 2001),5243-5275	
		ZUCKER, O , et al., "Application of Oxygen Plasma Processing to Silicon Direct Bonding", <u>Sensors and Actuators A</u> , 36, (1993),227-231	

EXAMINER

DATE CONSIDERED